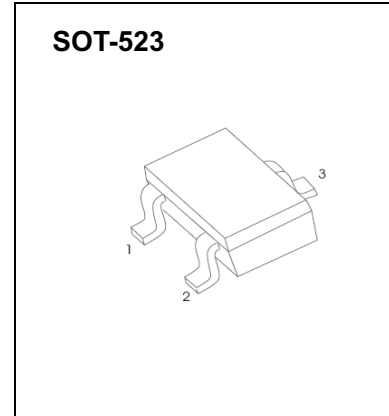




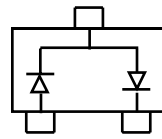
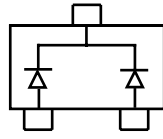
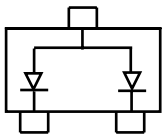
SOT-523 Plastic-Encapsulate Diodes

BAW56T/BAV70T/BAV99T SWITCHING DIODE



FEATURES

- ⌘ Fast Switching Speed
- ⌘ For General Purpose Switching Applications
- ⌘ High Conductance



BAW56T Marking: JD

BAV70T Marking: JJ

BAV99T Marking: JE

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Reverse voltage	V_R	85	V
Forward current	I_o	75	mA
Forward power dissipation	P_D	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C
Operation temperature	T_{op}	-40~+125	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 1\mu A$	85		V
Reverse voltage leakage current	I_{R1}	$V_R = 75V$		2	μA
	I_{R2}	$V_R = 25V$		0.03	μA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$	620 730 840 990	715 855 1000 1250	mV
Diode capacitance	C_D	$V_R = 0$ $f = 1MHz$		1.5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10mA$ $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$		4	ns



SOD-523 Plastic-Encapsulate Diodes

